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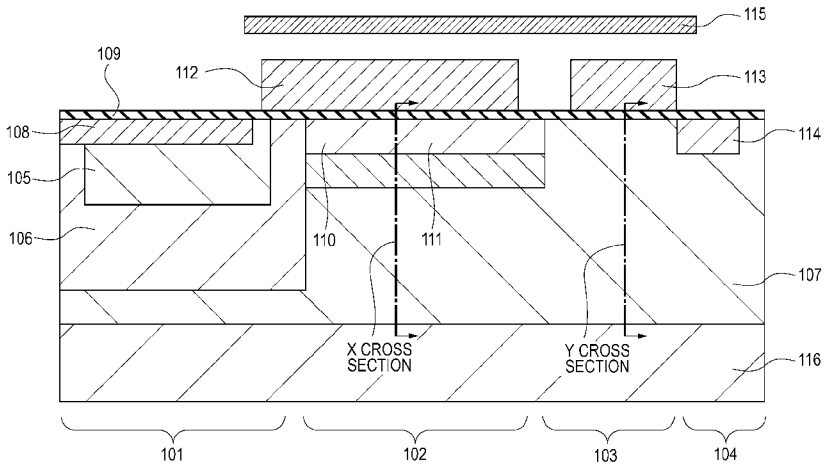
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(54) **Title**: SOLID-STATE IMAGE PICKUP DEVICE

[Fig. 1]



(57) **Abstract**: A photoelectric conversion portion, a charge holding portion, a transfer portion, and a sense node are formed in a P-type well. The charge holding portion is configured to include an N-type semiconductor region, which is a first semiconductor region holding charges in a portion different from the photoelectric conversion portion. A P-type semiconductor region having a higher concentration than the P-type well is disposed under the N-type semiconductor region.

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